

IN THE SPECIFICATION

Amend the specification by inserting, before the first line:

This is a continuation application of U.S. Serial No. 10/179,214, filed on June 26, 2002, which is a continuation application of U.S. Serial No. 09/969,847, filed October 4, 2001, now U.S. Patent No. 6,465,827, which is a continuation application of U.S. Serial No. 09/689,802, filed October 13, 2000, now U.S. Patent No. 6,441,416, which is a continuation application of U.S. Serial No. 09/665,062, filed September 19, 2000, abandoned, which is a divisional application of U.S. Serial No. 09/012,104, filed January 22, 1998, now U.S. Patent No. 6,147,374. This application is related to application Serial No. 09/969,848, filed October 4, 2001, now U.S. Patent No. 6,525,359.

Pages 2-3, the paragraph bridging these pages from page 2, line 25 to page 3, line 8, amend the paragraph as follows:

Capacitors having ferroelectric films are known to undergo deterioration of polarization characteristics upon their annealing in an atmosphere of hydrogen (Lecture Collections in '96 Ferroelectric Film Memory Technique Forum, published by K.K. Science Forum, [No. 4, page 4, lines 1-12])

Inc. Page 4-4). This deterioration is presumed to be caused by the platinum of upper and lower electrodes which reacts with hydrogen to act as a reducing catalyst to reduce the ferroelectric film. In particular, in the case of large-capacity highly integrated devices, the ferroelectric films are fine in size, and hence this deterioration of the characteristics of the capacitors is forecasted to greatly affect the characteristics of the overall devices.

Page 26, the first full paragraph, lines 2 to 17, the marked up paragraph is as follows:

The solder reflow resistance of the resin-encapsulated semiconductor apparatus was measured in the following way. First, the resin-encapsulated semiconductor apparatus was moistened by leaving it for 168 hours under the thermostatic hygrostatic conditions of 85°C and 85%. The resin-encapsulated semiconductor apparatus thus moistened was heated to a maximum temperature of 240 to 250°C for 10 seconds and then left to cool to room temperature, and this step was repeatedly carried out three times. Thereafter, using an ultrasonic flaw detector, any interfacial failure between the polyimide and the encapsulant resin was non-destructively observed to examine the solder reflow resistance of the surface-protective polyimide film. With regard to the temperature profile of an

infrared solder reflowing furnace, the temperature profile described in "Packaging Techniques for Surface Mount Type LSI Packages and Improvement in Its Reliability", p. 451 (compiled by Hitachi Ltd., Semiconductor & Integrated Circuits Division, published 1988) was [follwed] followed, setting a maximum temperature at 240 to 245°C.